Ordering number : ENA0436

SANYO Semiconductors
DATA SHEET

CPH3148 — PNP Epitaxial Planar Silicon Transistor
High-Voltage Switching Applications

Applications

- DC / DC converters, relay drivers, lamp drivers, motor drivers.

Features

- Adoption of FBET, MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Ultrasmall package permitting applied sets to be small and slim (mounting height: 0.9mm).
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		-100	V
Collector-to-Emitter Voltage	V_{CES}		-100	V
Collector-to-Emitter Voltage	V_{CEO}		-100	V
Emitter-to-Base Voltage	V_{EBO}		-7	V
Collector Current	I_C		-2	A
Collector Current (Pulse)	I_{CP}		-3	A
Base Current	I_B		-400	mA
Collector Dissipation	P_C	Mounted on a ceramic board (600mm²×0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=-80V, I_E=0A			-1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-4V, I_C=0A			-1	μA
DC Current Gain	h_{FE}	V_{CE}=-5V, I_C=-100mA	200		400	
Gain-Bandwidth Product	f_T	V_{CE}=-10V, I_C=-500mA		260		MHz
Output Capacitance	Cob	V_{CB}=-10V, f=1MHz		20		pF

Marking : BP

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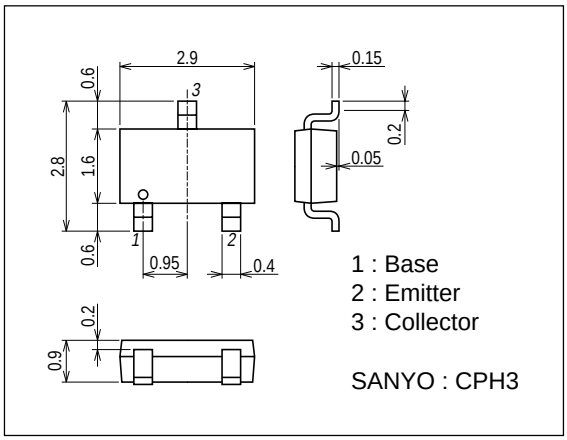
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=–1A, I_B=–100mA		–120	–240	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=–1A, I_B=–100mA		–0.85	–1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0A	–100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=–100μA, R_{BE}=0Ω	–100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–100			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=–10μA, I_C=0A	–7			V
Turn-ON Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	tstg	See specified Test Circuit.		600		ns
Fall Time	t_f	See specified Test Circuit.		30		ns

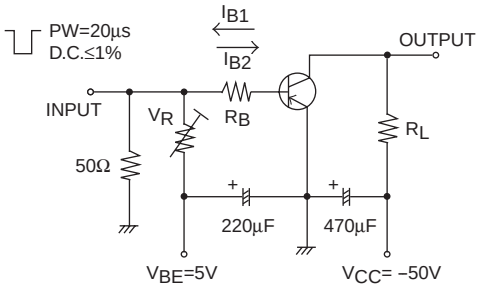
Package Dimensions

unit : mm (typ)

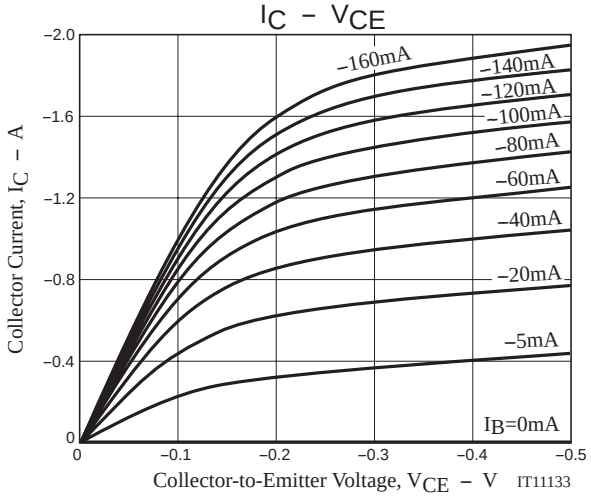
7015A-003

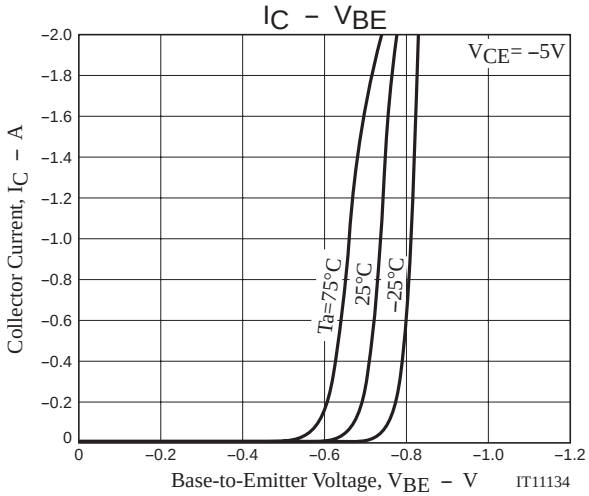


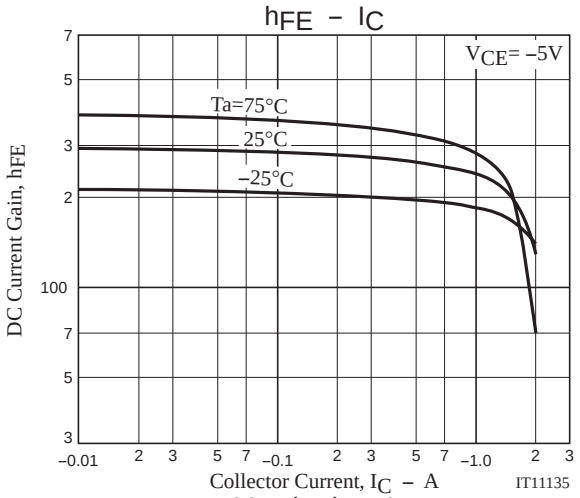
Switching Time Test Circuit

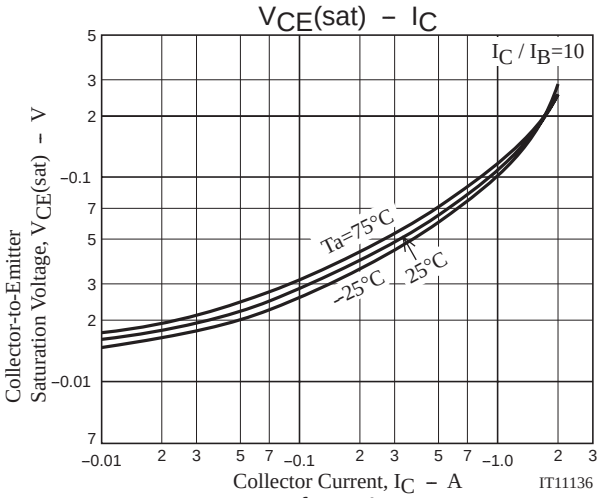


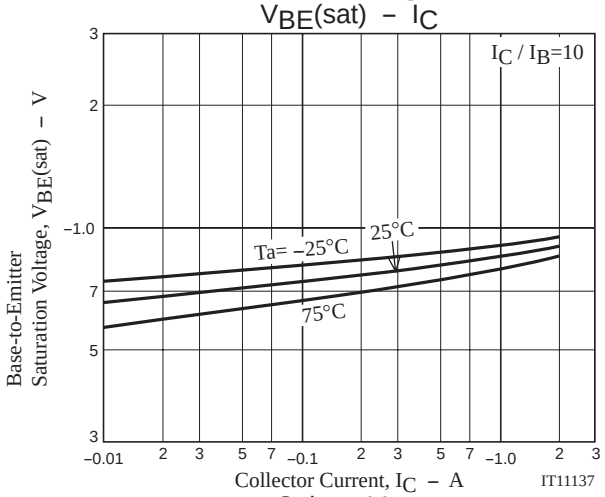
I_C= –10I_{B1}=10I_{B2}= –0.5A

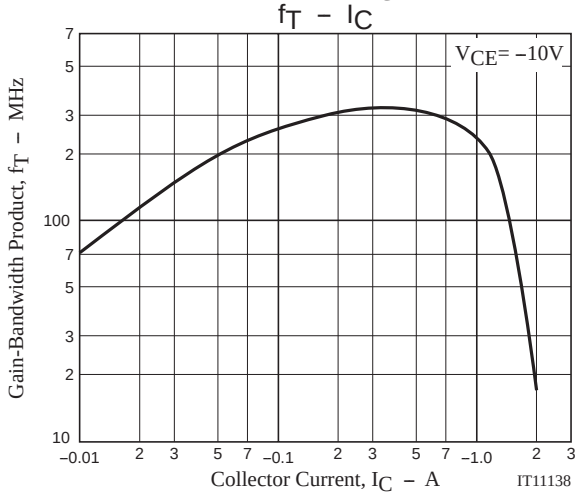


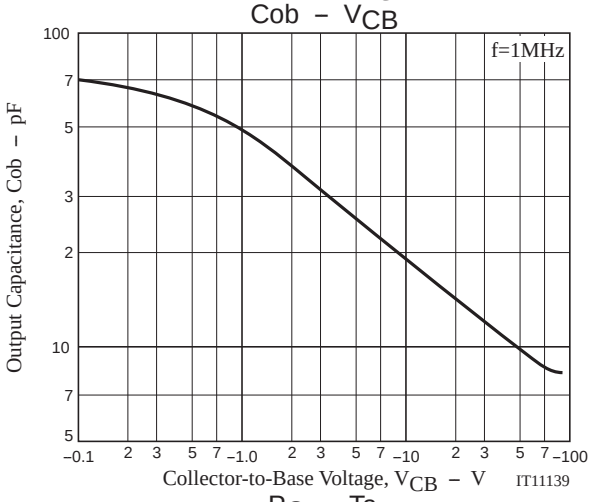


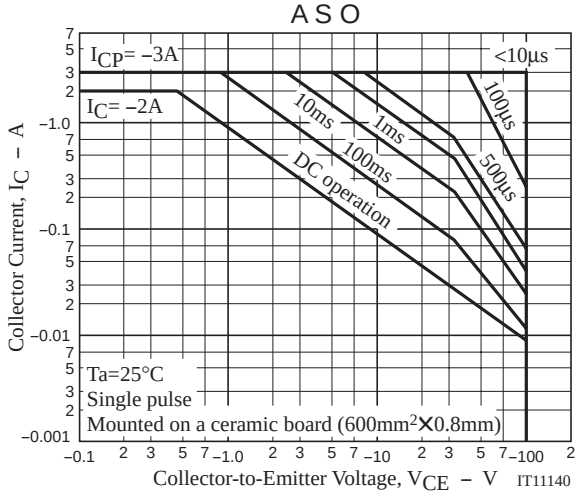

hFE – IC
VCE= –5V
Ta=75°C
25°C
–25°C
DC Current Gain, hFE
Collector Current, IC – A
IT11135

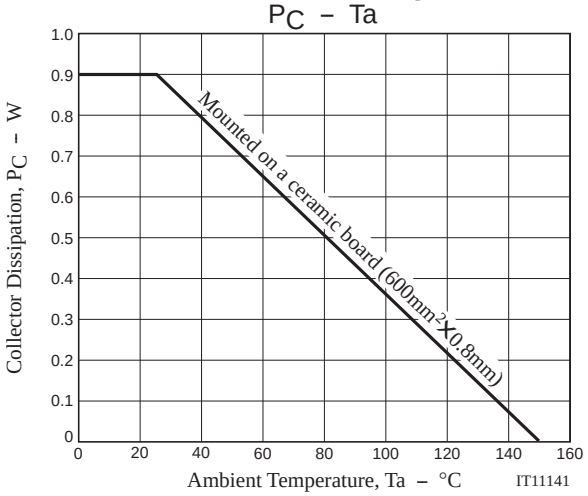

VCE(sat) – IC
IC / IB=10
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT11136


VBE(sat) – IC
IC / IB=10
Ta= –25°C
25°C
75°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT11137


fT – IC
VCE= –10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT11138


Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT11139


A S O
ICP= –3A
IC= –2A
<10µs
100µs
500µs
1ms
10ms
100ms
DC operation
Ta=25°C
Single pulse
Mounted on a ceramic board (600mm2×0.8mm)
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
IT11140


PC – Ta
Mounted on a ceramic board (600mm2×0.8mm)
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
IT11141